

N-Channel 800V (D-S) Super Junction Power MOSFET

PRODUCT SUMMARY		
V_{DS} (V) at T_J max.	800	
$R_{DS(on)}$ typ. at 25 °C (Ω)	$V_{GS} = 10$ V	0.38
Q_g max. (nC)	96	
Q_{gs} (nC)	11	
Q_{gd} (nC)	21	
Configuration	Single	

FEATURES

- Low figure-of-merit (FOM) $R_{on} \times Q_g$
- Low input capacitance (C_{iss})
- Reduced switching and conduction losses
- Ultra low gate charge (Q_g)
- Avalanche energy rated (UIS)

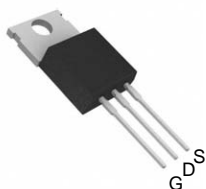


Available
RoHS*
Available

APPLICATIONS

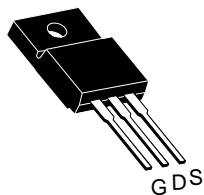
- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
 - High-intensity discharge (HID)
 - Fluorescent ballast lighting

TO-220-3L



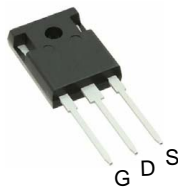
Top View

TO-220F-3L



Top View

DTN15N80SJ



Top View



N-Channel MOSFET

Package


DTP15N80SJ	DTP15N80FSJ	DTN15N80SJ
TO-220-3L	TO-220F-3L	TO-247-3L

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	800	V
Gate-Source Voltage	V_{GS}	± 30	
Continuous Drain Current ($T_J = 150$ °C)	V_{GS} at 10 V	$T_C = 25$ °C	15
		$T_C = 100$ °C	12
Pulsed Drain Current ^a	I_{DM}	46	A
Linear Derating Factor		1.7	W/°C
Single Pulse Avalanche Energy ^b	E_{AS}	297	mJ
Maximum Power Dissipation	P_D	208	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	°C
Drain-Source Voltage Slope	dV/dt	$T_J = 125$ °C	37
Reverse Diode dV/dt ^d		26	
Soldering Recommendations (Peak Temperature) ^c	for 10 s	300	°C

Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 50$ V, starting $T_J = 25$ °C, $L = 28.2$ mH, $R_g = 25$ Ω , $I_{AS} = 4.5$ A.
- 1.6 mm from case.
- $I_{SD} \leq I_D$, $dI/dt = 100$ A/ μ s, starting $T_J = 25$ °C.

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	62	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.7	

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		800	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$, $I_D = 1\text{ mA}$		-	0.75	-	V/°C
Gate-Source Threshold Voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		2	-	4	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$		-	-	± 100	nA
		$V_{GS} = \pm 30\text{ V}$		-	-	± 1	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}$		-	-	1	μA
		$V_{DS} = 520\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		-	-	10	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 8\text{ A}$	-	0.38	0.45	Ω
Forward Transconductance	g_{fs}	$V_{DS} = 30\text{ V}, I_D = 8\text{ A}$		-	6.3	-	S
Dynamic							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V},$ $V_{DS} = 100\text{ V},$ $f = 1\text{ MHz}$		-	1720	-	pF
Output Capacitance	C_{oss}			-	80	-	
Reverse Transfer Capacitance	C_{rss}			-	4	-	
Effective Output Capacitance, Energy Related ^a	$C_{o(er)}$	$V_{DS} = 0\text{ V to } 520\text{ V}, V_{GS} = 0\text{ V}$		-	63	-	
Effective Output Capacitance, Time Related ^b	$C_{o(tr)}$			-	213	-	
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}$	$I_D = 8\text{ A}, V_{DS} = 520\text{ V}$	-	48	96	nC
Gate-Source Charge	Q_{gs}			-	11	-	
Gate-Drain Charge	Q_{gd}			-	21	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 520\text{ V}, I_D = 8\text{ A},$ $V_{GS} = 10\text{ V}, R_g = 9.1\text{ }\Omega$		-	18	36	ns
Rise Time	t_r			-	24	48	
Turn-Off Delay Time	$t_{d(off)}$			-	48	96	
Fall Time	t_f			-	25	50	
Gate Input Resistance	R_g	$f = 1\text{ MHz}, \text{ open drain}$		-	0.8	-	Ω
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	15	A
Pulsed Diode Forward Current	I_{SM}			-	-	46	
Diode Forward Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = 8\text{ A}, V_{GS} = 0\text{ V}$		-	-	1.2	V
Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = I_S = 8\text{ A},$ $dI/dt = 100\text{ A}/\mu\text{s}, V_R = 400\text{ V}$		-	325	-	ns
Reverse Recovery Charge	Q_{rr}			-	4.6	-	μC
Reverse Recovery Current	I_{RRM}			-	20	-	A

Notes

- a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS} .
- b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS} .

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

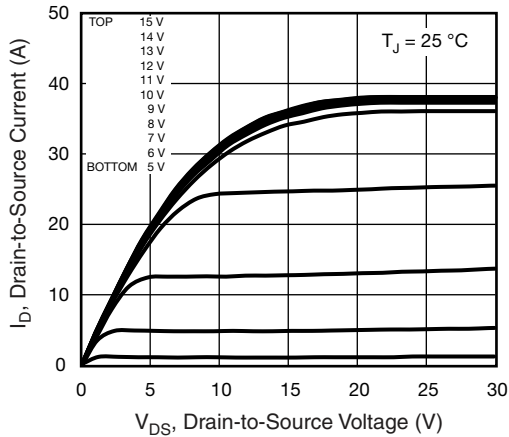


Fig. 1 - Typical Output Characteristics

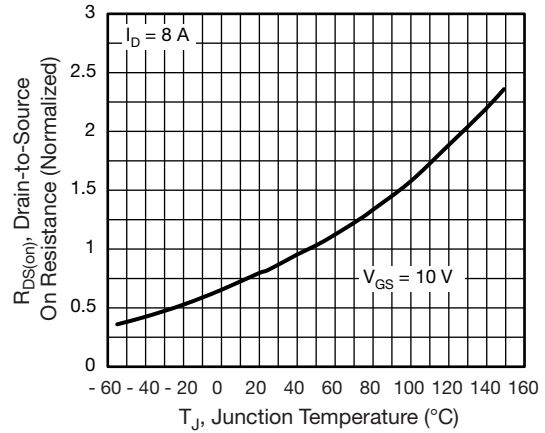


Fig. 4 - Normalized On-Resistance vs. Temperature

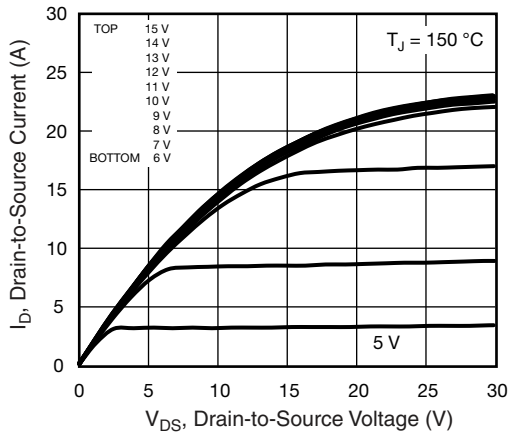


Fig. 2 - Typical Output Characteristics

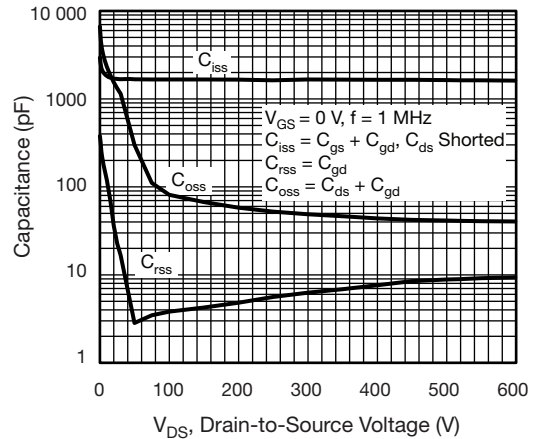


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

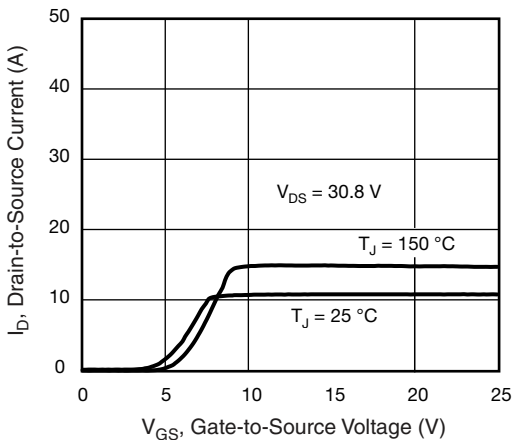


Fig. 3 - Typical Transfer Characteristics

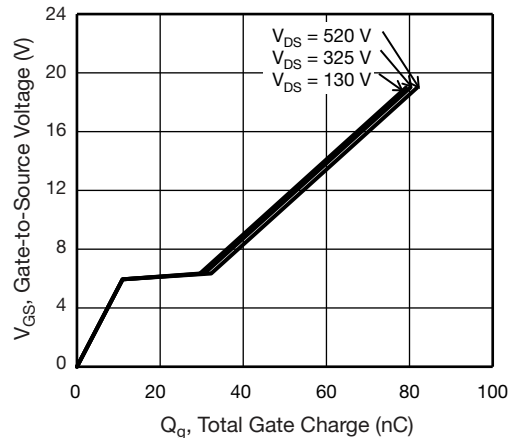


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

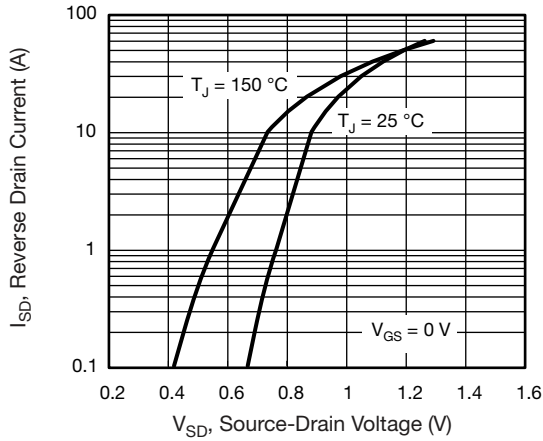


Fig. 7 - Typical Source-Drain Diode Forward Voltage

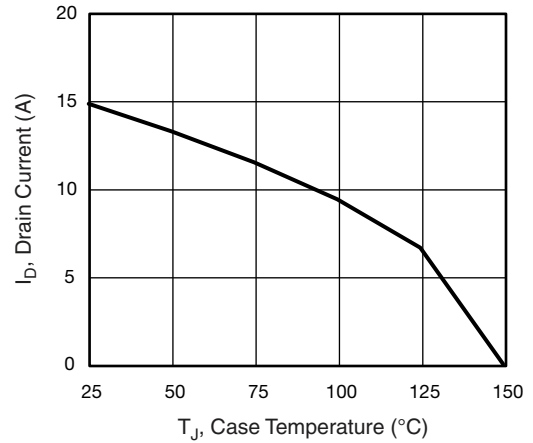


Fig. 9 - Maximum Drain Current vs. Case Temperature

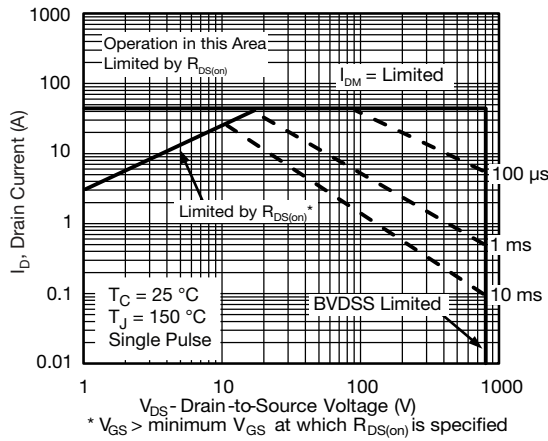


Fig. 8 - Maximum Safe Operating Area

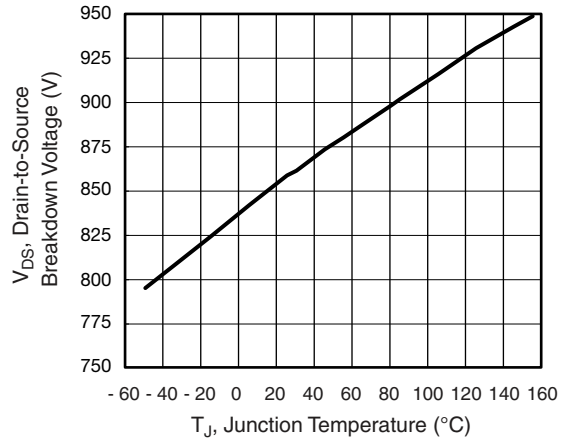


Fig. 10 - Temperature vs. Drain-to-Source Voltage

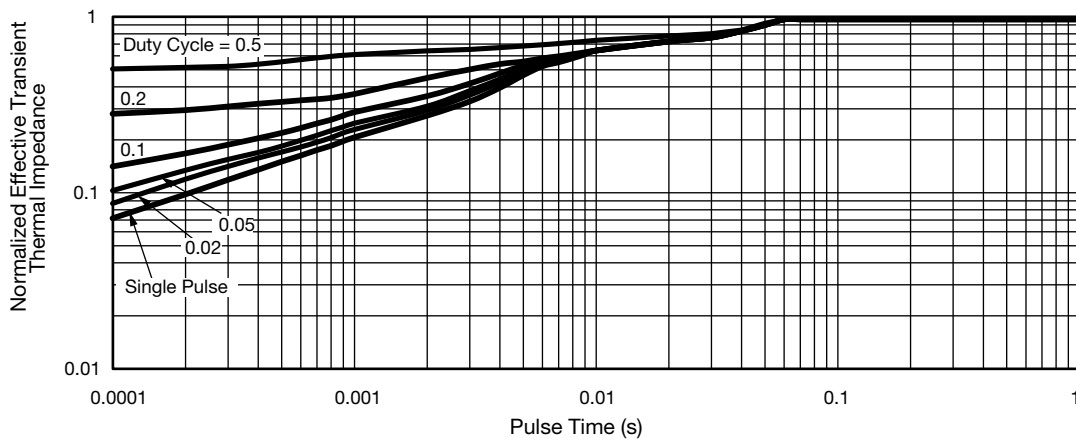


Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case

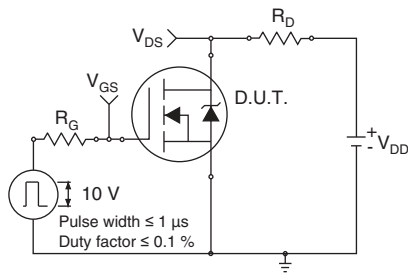


Fig. 12 - Switching Time Test Circuit

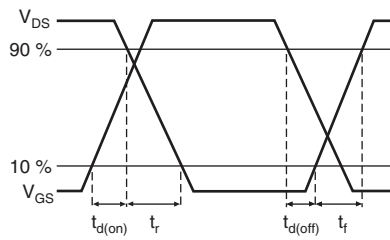


Fig. 13 - Switching Time Waveforms

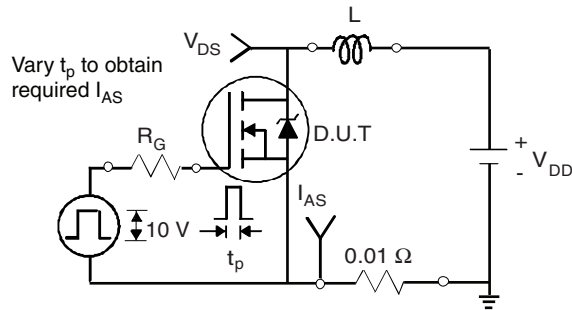


Fig. 14 - Unclamped Inductive Test Circuit

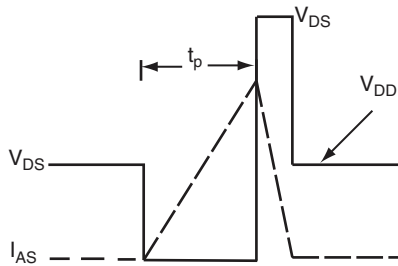


Fig. 15 - Unclamped Inductive Waveforms

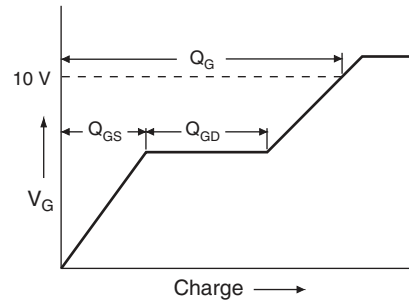


Fig. 16 - Basic Gate Charge Waveform

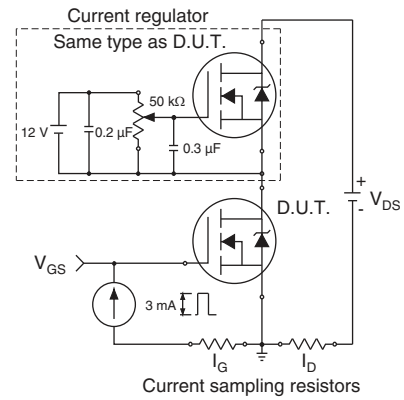
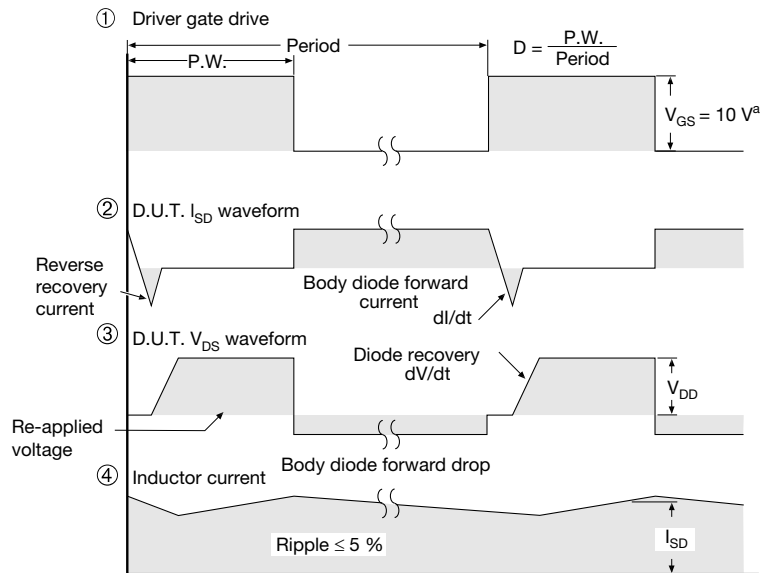
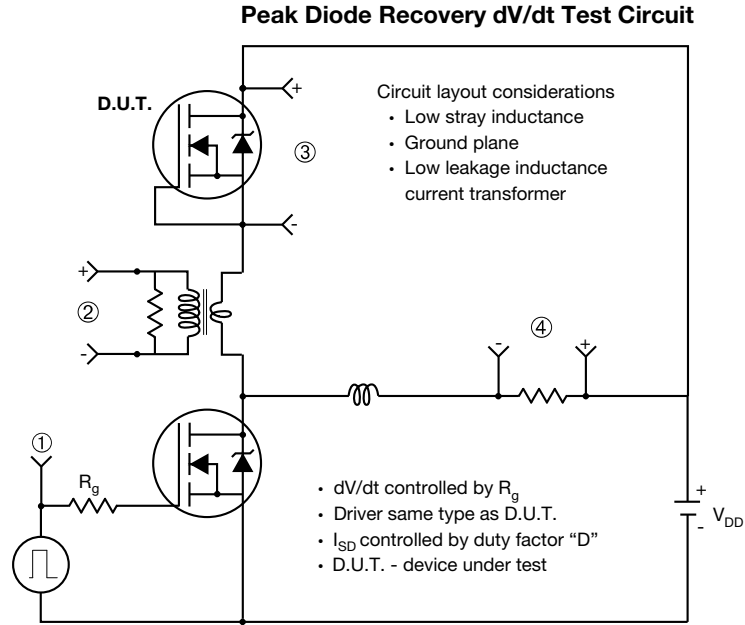


Fig. 17 - Gate Charge Test Circuit

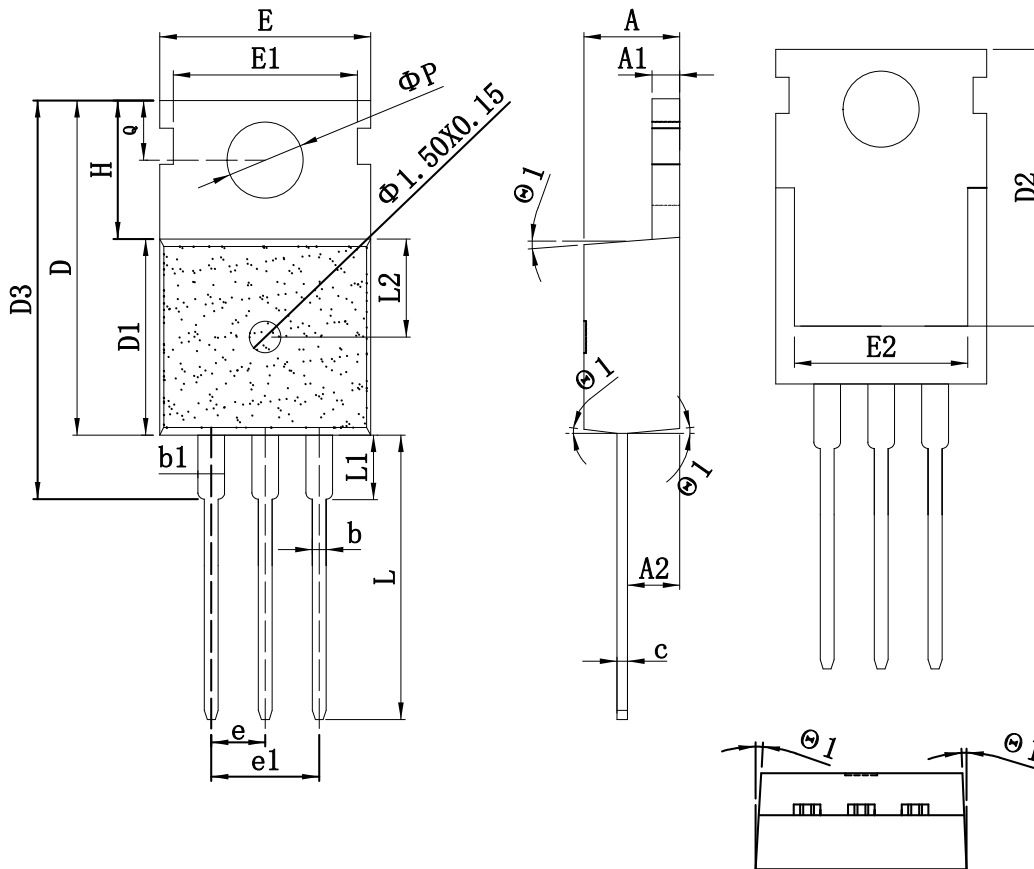


Note

a. $V_{GS} = 5 V$ for logic level devices

Fig. 18 - For N-Channel

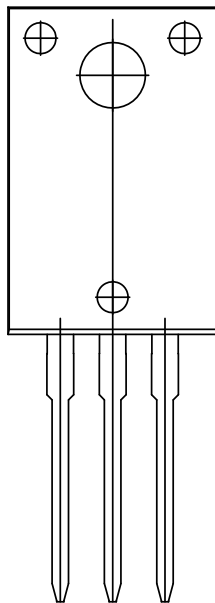
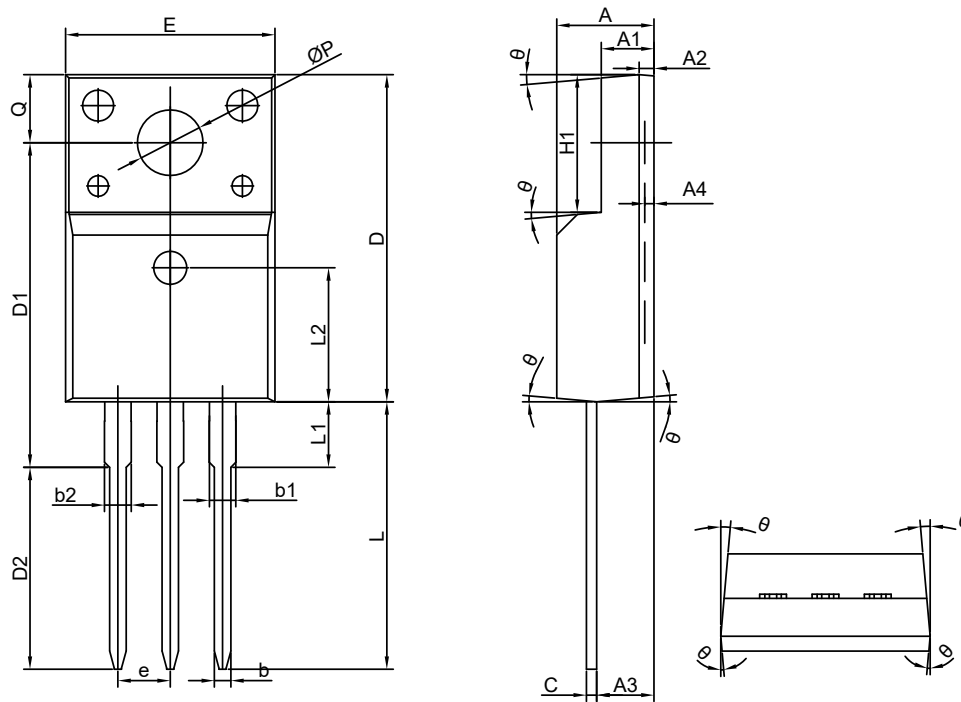
TO-220_3L PACKAGE OUTLINE



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	mm			SYMBOL	mm		
	MIN	TYP	MAX		MIN	TYP	MAX
A	4.15	4.50	4.80	E1	8.25	8.70	9.15
A1	1.15	1.30	1.50	E2	7.20	8.00	8.80
A2	2.10	2.40	2.65	e	2.38	2.54	2.74
b	0.65	0.80	1.00	e1	5.08REF		
b1	1.10	1.33	1.80	H	6.20	6.50	6.90
c	0.35	0.50	0.65	L	12.75	13.28	13.70
D	14.25	15.75	16.15	L1	-	-	3.50
D1	8.70	9.20	9.60	L2	2.30	4.65	7.00
D2	12.30	13.10	13.85	ϕP	3.40	3.65	3.85
D3	16.20	18.80	20.60	Q	2.50	2.80	3.00
E	8.68	10.02	11.00	θ	2°	-	7°

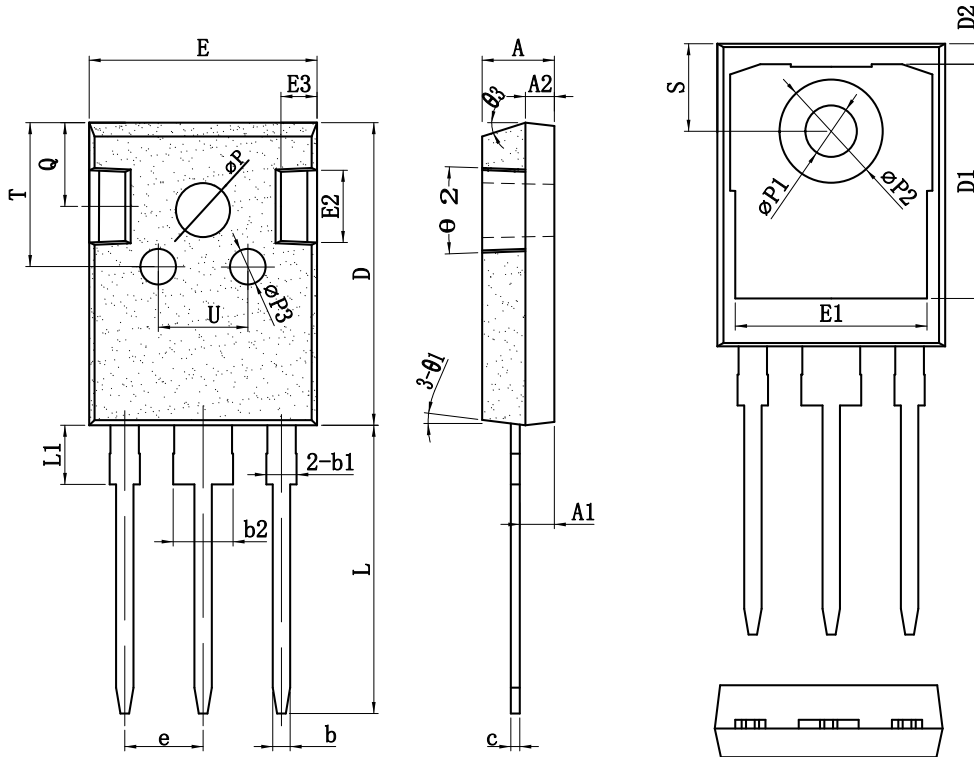
TO-220F_3L PACKAGE OUTLINE



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	4.30	4.72	5.10
A1	2.25	2.56	2.90
A2	0.72 REF		
A3	2.28	2.78	3.50
A4	0.45 MAX		
b	0.65	-	0.95
b1	1.00	-	1.55
b2	-	-	1.55
c	0.40	0.50	0.65
D	15.47	15.87	16.37
D1	15.35	15.75	16.25
E	9.76	10.16	10.76
e	2.54 BSC		
H1	6.28	6.68	7.08
L	12.48	12.98	13.50
L1	2.90	-	3.80
L2	2.54 BSC		
ØP	2.98	3.18	3.50
Q	3.00	-	3.60
θ	3°	5°	7°

TO-247_3L PACKAGE OUTLINE



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	TYP	MAX	SYMBOL	MIN	TYP	MAX
A	4.60	5.00	5.40	e	2.10	5.44	5.70
A1	2.10	2.41	2.70	L	19.00	19.98	21.00
A2	1.70	2.00	2.30	L1	-	-	4.50
b	1.00	1.20	1.40	ΦP	3.30	3.70	4.00
b1	1.80	2.10	2.40	$\Phi P1$	3.25	3.55	3.85
b2	2.80	3.10	3.40	$\Phi P2$	6.80	7.18	7.60
C	0.45	0.60	0.75	$\Phi P3$	2.30	2.50	3.30
D	19.00	21.00	23.00	Q	5.50	5.80	6.30
D1	16.00	16.55	17.00	S	5.60	6.15	6.30
D2	0.95	1.20	1.45	T	9.50	10.00	10.50
E	15.70	15.80	16.50	U	6.00	-	8.00
E1	12.80	13.25	13.70	$\theta 1$	5°	7°	9°
E2	4.20	5.00	5.30	$\theta 2$	1°	3°	5°
E3	2.20	2.50	2.80	$\theta 3$	13°	15°	17°

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